

<b>Form PTO-1449 U.S. Department of Commerce (REV. 2-82) Patent and Trademark Office</b>  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use several sheets if necessary)	Atty. Docket No. 070050.2717	Serial No. 10/525,297
	Applicant James S. Im	
	Filing Date 2/15/2005	Group <b>2811 2822</b>
	Examiner Bac H. Au	

## FOREIGN PATENT DOCUMENTS

NY02:587010.1

**Examiner**

/Bac Au/

### Date Considered

07/31/2007

\* Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

DT13 Rec'd PCT/PTO 15 FEB 2005 10/525297

PTO/SB/08A (08-03)

Approved for use through 07/31/2006, OMB 0651-0031

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

**Substitute for form 1449/PTO**

## **INFORMATION DISCLOSURE STATEMENT BY APPLICANT**

*(Use as many sheets as necessary)*

Sheet 1 of 1

**Complete if Known**

Application Number	Not yet assigned 10/525297
Filing Date	Herewith 2/15/2005
First Named Inventor	James S. Im
Art Unit	Not yet assigned 2822
Examiner Name	Not yet assigned Bac H. Au
Attorney Docket Number	A35413-PCT-USA (070050.2717)

## U. S. PATENT DOCUMENTS

## FOREIGN PATENT DOCUMENTS

**Examiner  
Signature**

/Bac Au/

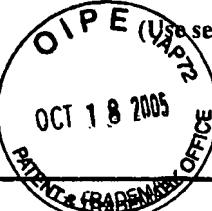
Date  
Considered

07/26/2007

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 801.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.

Form PTO-1449 U.S. Department of Commerce (REV. 2-82) Patent and Trademark Office		Atty. Docket No. A35413-PCT-USA (070050.2717)	Serial No. 10/525,297
<b>INFORMATION DISCLOSURE STATEMENT</b> <b>BY APPLICANT</b> <div style="text-align: center;">(Use several sheets if necessary)</div> <div style="text-align: right; margin-top: -20px;">  </div>			
Applicant James S. Im			
Filing Date 02/15/2005		Group 284 2822	
Examiner Not yet assigned Bac H. Au			

### U.S. PATENT DOCUMENTS

Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
/BA/	1	3632205	01/04/1972	Marcy
	2	4234358	11/18/1980	Celler et al.
	3	4309225	01/05/1982	Fan et al. Duplicate
	4	4382658	05/10/1983	Shields et al.
	5	4456371	06/1984	Lin
	6	4639277	01/27/1987	Hawkins
	7	4691983	09/08/1987	Kobayashi et al.
	8	4727047	02/1988	Bolzer et al.
	9	4758533	07/1988	Magee et al.
	10	4793694	12/27/1988	Liu
	11	4800179	01/1989	Mukai
	12	4855014	08/1989	Kakimoto et al.
	13	4870031	09/1989	Suguhara et al.
	14	4940505	07/1990	Schachmeyer et al.
▼	15	4970546	11/1990	Suzuki et al.

NY02:531132.1

Examiner

/Bac Au/

Date Considered

07/26/2007

\* Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449 U.S. Department of Commerce (REV. 2-82) Patent and Trademark Office		Atty. Docket No. A35413-PCT-USA (070050.2717)	Serial No. 10/525,297
INFORMATION DISCLOSURE STATEMENT BY APPLICANT			
(Use several sheets if necessary)			
		Applicant James S. Im	
		Filing Date 02/15/2005	Group 20++ 2822
		Examiner <del>Not yet assigned</del> Bac H. Au	

Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
/BA/	16	4977104	12/11/1990	Sawada et al.
	17	5032233	07/1991	Yu et al.
	18	5061655	10/1991	Ipposhi et al.
	19	5145808	09/1992	Sameshima et al.
	10	5204659	04/1993	Sarma
	21	5233207	08/1993	Anzai
	22	5285236	02/08/1994	Jain
	23	5291240	03/1994	Jain
	24	5304357	04/19/1994	Sato et al.
	25	5373803	12/1994	Noguchi et al.
	26	5395481	03/1995	McCarthy
	27	5409867	04/1995	Asano
	28	5453594	08/1995	Konecny
	29	5456763	10/1995	Kaschmitter et al.
	30	5496768	03/1996	Kudo
▼	31	5523193	06/1996	Nelson

NY02:531132.1

Examiner /Bac Au/	Date Considered 07/26/2007
----------------------	-------------------------------

\* Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449 U.S. Department of Commerce (REV. 2-82) Patent and Trademark Office		Atty. Docket No. A35413-PCT-USA (070050.2717)	Serial No. 10/525,297
INFORMATION DISCLOSURE STATEMENT BY APPLICANT  (Use several sheets if necessary)		Applicant James S. Im	
		Filing Date 02/15/2005	Group 2811 2822
		Examiner Not yet assigned Bac H. Au	

Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
/BA/	32	5529951	06/1996	Noguchi et al.
	34	5591668	01/1997	Macgawa et al. Duplicate
	35	5721606	02/01/1998	Jain
	36	5742426	04/1998	York
	37	5756364	05/1998	Tanaka et al.
	38	5766989	06/1998	Macgawa et al. Duplicate
	39	5844588	12/1998	Anderson
	40	5861991	01/1999	Fork
	41	5893990	04/1999	Tanaka
	42	5986807	11/1999	Fork
	43	6014944	01/18/2000	Russell et al.
	44	6072631	06/2000	Guenther et al.
	45	6081381	06/2000	Shalapenok et al.
	46	6117752	09/12/2000	Suzuki.
	47	6120976	09/2000	Treadwell et al.
▼	48	6130009	10/2000	Smith et al.

NY02:531132.1	
Examiner /Bac Au/	Date Considered 07/26/2007

\* Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449 U.S. Department of Commerce (REV. 2-82) Patent and Trademark Office		Atty. Docket No. A35413-PCT-USA (070050.2717)	Serial No. 10/525,297
INFORMATION DISCLOSURE STATEMENT BY APPLICANT  (Use several sheets if necessary)		Applicant James S. Im	
		Filing Date 02/15/2005	Group 2811 2822
		Examiner <del>Not yet assigned</del> Bac H. Au	

Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
/BA/	49	6130455	10/10/2000	Yoshinouchi
	50	6156997	12/2000	Yamazaki et al.
	51	6162711	12/19/2000	Ma et al.
	52	<del>6169014</del>	01/2001	McCulloch Duplicate
	53	6172820	01/2001	Kuwahara.
	54	6177301	01/2001	Jung
	55	6187088	02/01/2001	Okumura
	56	6190985	02/2001	Buynoski
	57	6193796	02/01/2001	Yang
	58	6203952	03/2001	O'Brien et al.
	59	6235614	02/01/2001	Yang
	60	6242291	06/2001	Kusumoto et al.
	61	6285001	09/2001	Fleming et al.
	62	6300175	10/2001	Moon
	63	6313435	11/2001	Shoemaker et al.
▼	64	6316338	11/2001	Jung

NY02:531132.1			
Examiner	/Bac Au/	Date Considered	07/26/2007

\* Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<b>Form PTO-1449 U.S. Department of Commerce (REV. 2-82) Patent and Trademark Office</b> <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <b>(Use several sheets if necessary)</b>		Atty. Docket No. A35413-PCT-USA (070050.2717)	Serial No. 10/525,297
		Applicant James S. Im	
		Filing Date 02/15/2005	Group 2011 2822
		Examiner <del>Not yet assigned</del> Bac H. Au	

Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
/BA/	65	6320227	11/2001	Lee et al.
	66	6322625	11/2001	Im
	67	6326186	12/2001	Park et al. Kirk et al.
	68	6326286	12/2001	Park et al.
	69	6333232	12/2001	Kunikiyo
	70	6368945	04/09/2002	Im
	71	6388146	05/14/2002	Onishi et al.
	72	6407012	06/18/2002	Miyasaka et al.
	73	6444506	09/2002	Kusumoto et al.
	74	6468845	10/22/2002	Nakajima et al.
	75	6495067	12/17/2002	Ono
	76	6511718	01/18/2003	Paz de Araujo et al.
	77	6521492	02/18/2003	Miyasaka et al.
	78	6528359	03/2003	Kusumoto et al.
	79	6555449	04/2003	Im et al.
✓	80	6573531	06/2003	Im et al.

NY02:531132.1

Examiner /Bac Au Date Considered 07/26/2007

\* Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449 U.S. Department of Commerce (REV. 2-82) Patent and Trademark Office		Atty. Docket No. A35413-PCT-USA (070050.2717)	Serial No. 10/525,297
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Applicant James S. Im	
(Use several sheets if necessary)		Filing Date 02/15/2005	Group 28H 2822
		Examiner Not yet assigned Bac H. Au	

Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
/BA/	81	6621044	09/01/2003	Jain et al.
	82	6635554	10/2003	Im et al.
	83	6526585	03/04/2003	Hill
	84	20010001745	05/24/2001	Im et al.
	85	20010041426	11/15/2001	Im
	86	20040053450	03/18/2004	Sposili et al.
	87	20020104750	08/08/2002	Ito
	88	RE33836	03/03/1992	Resor, III et al.
	89	60/253256	08/31/2003	Im
	123	2003096489 20030096489	05/22/2003	Im et al.
	124	2003119286 20030119286	06/26/2003	Im et al.
	125	20050032249 20050032249	02/10/2005	Im et al.
	126	2003029212 20030029212	02/13/2003	Im
	127	2004061843 20040061843	04/01/2004	Im
	128	20050034653 20050034653	02/17/2005	Im et al.
▼	129	6563077	05/13/2003	Im

NY02:531132.1

Examiner

/Bac Au/

Date Considered

07/26/2007

\* Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<b>Form PTO-1449 U.S. Department of Commerce (REV. 2-82) Patent and Trademark Office</b>		Atty. Docket No. A35413-PCT-USA (070050.2717)	Serial No. 10/525,297
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>			
<b>(Use several sheets if necessary)</b>			
		Applicant James S. Im	
		Filing Date 02/15/2005	Group 2811 2822
		Examiner <del>Not yet assigned</del> Bac H. Au	

Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
/BA/	130	6582827	06/24/2003	Im
/BA/	33	6830993	12/14/2004	Im et al.

NY02:531132.1

Examiner

/Bac Au/

Date Considered

07/26/2007

Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449 U.S. Department of Commerce (REV. 2-82) Patent and Trademark Office		Atty. Docket No. A35413-PCT-USA (070050.2717)	Serial No. 10/525,297
INFORMATION DISCLOSURE STATEMENT BY APPLICANT			
(Use several sheets if necessary)			
		Applicant James S. Im	
		Filing Date 02/15/2005	Group 2811 2822
		Examiner Not yet assigned Bac H. Au	

## FOREIGN PATENT DOCUMENTS

Exam Initial	No.	Document No.	Publication Date	Country	Translation
					Yes No
/BA/	90	681316	08/11/1995	EP	
	91	1067593	10/01/2001	EP	
	92	655774	07/17/1996	EP	
	93	2338343	12/15/1999	GB	
	94	2338597	12/22/1999	GB	
	95	2338342	12/15/1999	GB	
	96	2283036	11/20/1990	JP	<u>No</u>
	97	6252048	09/09/1994	JP	<u>No</u>
	98	6283422	10/07/1994	JP	<u>No</u>
	99	7176757	07/14/1995	JP	<u>No</u>
	100	11064883	03/05/1999	JP	<u>No</u>
	101	04033327		JP	<u>No</u>
	102	2001023920	01/26/2001	JP	
	103	62181419	08/08/1987	JP	
▼	104	9824118	06/04/1998	WO	

NY02:531132.1	/Bac Au/	Date Considered	07/31/2007
---------------	----------	-----------------	------------

\* Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449 U.S. Department of Commerce (REV. 2-82) Patent and Trademark Office		Atty. Docket No. A35413-PCT-USA (070050.2717)	Serial No. 10/525,297
INFORMATION DISCLOSURE STATEMENT BY APPLICANT			
(Use several sheets if necessary)			
		Applicant James S. Im	
		Filing Date 02/15/2005	Group 28++ 2822
		Examiner <del>Not yet assigned</del> Bac H. Au	

Exam Initial	No.	Document No.	Publication Date	Country	Translation Yes No
/BA/	105	9931719	06/24/1999	WO	No
	106	0014784	03/16/2000	WO	
	107	0118854	03/15/2001	WO	
	108	0118855	03/15/2001	WO	
	109	0171786	09/27/2001	WO	
	110	02031869	04/18/2002	WO	
	111	02086954	05/30/2002	WO	
	112	9745827	12/04/1997	WO	
	113	0242847	05/30/2002	WO	
	114	03046965	06/05/2003	WO	
	115	02086955	10/31/2002	WO	
	116	03018882	03/06/2003	WO	
	117	04017379	02/26/2004	WO	
	118	03084688	10/16/2003	WO	
	119	04017382	02/26/2004	WO	
▼	120	04017381	02/26/2004	WO	

NY02:531132.1

Examiner

/Bac Au/

Date Considered

07/31/2007

\* Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<b>Form PTO-1449 U.S. Department of Commerce (REV. 2-82) Patent and Trademark Office</b>		Atty. Docket No. A35413-PCT-USA (070050.2717)	Serial No. 10/525,297
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>			
<b>(Use several sheets if necessary)</b>			
		Filing Date 02/15/2005	Group 2011 2822
		Examiner <del>Not yet assigned</del> Bac H. Au	

Exam Initial	No.		Document No.	Publication Date	Country	Translation	
						Yes	No
/BA/	121		04017380	02/26/2004	WO		
/BA/	122		04075263	08/19/2003	WO		

NY02:531132.1

Examiner

/Bac Au/

Date Considered

07/31/2007

Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449 U.S. Department of Commerce (REV. 2-82) Patent and Trademark Office		Atty. Docket No. A35413-PCT-USA (070050.2717)	Serial No. 10/525,297
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use several sheets if necessary)		Applicant James S. Im	
		Filing Date 02/15/2005	Group <del>281</del> 2822
		Examiner <del>Not yet assigned</del> Bac H. Au	

Exam Initial	No.	OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)	
/BA/	132	Im et al., "Controlled Super-Lateral Growth of Si Films for Microstructural Manipulation and Optimization", Phys. Stat. Sol. (a), vol. 166, p. 603 (1998).	
	133	S.D. Brotherton et al., "Influence of Melt Depth in Laser Crystallized Poly-Si Thin Film Transistors," 82 J. Appl. Phys. 4086 (1997).	
	134	J.S. Im et al., "Crystalline Si Films for Integrated Active-Matrix Liquid-Crystals Displays," 21 MRS Bulletin 39 (1996).	
	135	Im et al., "Single-Crystal Si Films for Thin-Film Transistor Devices," Appl. Phys. Lett., Vol 70 (25), p. 3434 (1997).	
	136	Sposili et al., "Sequential Lateral Solidification of Thin Silicon Films on SiO <sub>2</sub> ", Appl. Phys. Lett., vol. 69 (19), p. 2864 (1996).*	
	137	Crowder et al., "Low-Temperature Single-Crystal Si TFT's Fabricated on Si Films processed via Sequential Lateral Solidification", IEEE Electron Device Letter, vol. 19 (8), p. 306 (1998).*	
	138	Sposili et al., "Single-Crystal Si Films via a Low-Substrate-Temperature Excimer-Laser Crystallization Method", Mat. Res. Soc. Symp. Proc. vol. 452, pp. 953-958, 1997 Materials Research Society.*	
	139	C. E. Nebel, "Laser Interference Structuring of A-Si:h" Amorphous Silicon Technology--1996, San Francisco, CA Apr. 8-12, 1996, Materials Research Society Symposium Proceedings, vol. 420, Pittsburgh, PA.	
	140	J. H. Jeon et al., "Two-step laser recrystallization of poly-Si for effective control of grain boundaries", Journal of Non Crystalline Solids, North-Holland Publishing Company, NL, vol. 266-269, May 2000, pp. 645-649.	
	141	H. Endert et al., "Excimer Laser: A New Tool for Precision Micromaching," 27 Optical and Quantum Electronics, 1319 (1995).	
✓	142	"Overview of Beam Delivery Systems for Excimer Lasers," Micro/Las Lasersystem GMBH. 1999	

NY02:531132.1

Examiner

/Bac Au/

Date Considered

07/31/2007

\* Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449 U.S. Department of Commerce (REV. 2-82) Patent and Trademark Office		Atty. Docket No. A35413-PCT-USA (070050.2717)	Serial No. 10/525,297
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use several sheets if necessary)		Applicant James S. Im	
		Filing Date 02/15/2005	Group 2011 2822
		Examiner <del>Not yet assigned</del> Bac H. Au	

Exam Initial	No.	OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)	
/BA/	143	K.H. Weiner et al., "Ultrashallow Junction Formation Using Projection Gas Immersion Laser Doping (PGILD)," A Verdant Technologies Technical Brief, Aug. 20, 1997.	
	144	Hau-Riege C.S. et al., "The Effects Microstructural Transitions at Width Transitions on interconnect reliability," Journal of Applied Physics, June 15, 2000, vol. 87, no. 12, pp. 8467-8472	
	145	McWilliams et al., "Wafer-Scale Laser Pantography: Fabrication of N-Metal-Oxide-Semiconductor Transistors and Small-Scale Integrated Circuits By Direct-Write Laser-Induced Pyrolytic Reactions," Applied Physics Letters, American Institute of Physics, New York, US, vol. 43, no. 10, Nov. 1983, pp. 946-948	
	146	Mariucci et al., "Grain boundary location control by patterned metal film in excimer laser crystallized polysilicon," Proceedings of the Fifth International Conference on Polycrystalline Semiconductors, Schwabisch Gmund, Germany, Sept. 13-18, 1998, vol. 67-68, pp. 175-180	
	147	Broadbent et al., "Excimer Laser Processing of Al-1%Cu/TiW Interconnect Layers," 1989 Proceedings, Sixth International IEEE VLSI Multilevel Interconnection Conference, Santa Clara, CA, June 12-13, 1989, pp. 336-345	
	148	H.J. Kim and James S. Im, "Grain Boundary Location-Controlled Poly-Si Films for TFT Devices Obtained Via Novel Excimer Laser Process," Abstracts for Symposium of Materials Research Society, Nov. 27 to Dec. 2, 1994, p. 230.	
	149	S.D. Brotherton, "Polycrystalline Silicon Thin Film Transistors," 10 Semicond. Sci. Tech., pp. 721-738 (1995).	
	150	H. Watanabe et al., "Crystallization Process of Polycrystalline Silicon by KrF Excimer Laser Annealing," 33 Japanese J. of Applied Physics Part 1--Regular Papers Short Notes & Review Papers, pp. 4491-98 (1994).	
	151	E. Fogarassy et al., "Pulsed Laser Crystallization of Hydrogen-Free a-Si Thin Films for High-Mobility Poly-Si TFT Fabrication," 56 Applied Physics A--Solids and Surfaces, pp. 365-373 (1993).	
	152	Y. Miyata et al., "Low-Temperature Polycrystalline Silicon Thin-Film Transistors for Large-Area Liquid Crystal Display," 31 Japanese J. of Applied Physics Part 1--Regular Papers Short Notes & Review Papers, pp. 4559-62 (1992).	
✓	153	Im et al., "Phase Transformation Mechanisms Involved in Excimer Laser Crystallization of Amorphous Silicon Films," Appl. Phys. Lett., Vol. 63 (14), p. 1969 (1993).	

NY02:531132.1

Examiner

/Bac Au/

Date Considered

07/31/2007

\* Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<b>Form PTO-1449 U.S. Department of Commerce (REV. 2-82) Patent and Trademark Office</b>																	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>																	
<b>(Use several sheets if necessary)</b>																	
<table border="1"> <tr> <td colspan="2">Atty. Docket No. A35413-PCT-USA (070050.2717)</td> <td>Serial No. 10/525,297</td> </tr> <tr> <td colspan="3">Applicant James S. Im</td> </tr> <tr> <td>Filing Date 02/15/2005</td> <td>Group 28++ 2822</td> <td></td> </tr> <tr> <td>Examiner Not yet assigned</td> <td>Bac H. Au</td> <td></td> </tr> <tr> <td colspan="3"></td> </tr> </table>			Atty. Docket No. A35413-PCT-USA (070050.2717)		Serial No. 10/525,297	Applicant James S. Im			Filing Date 02/15/2005	Group 28++ 2822		Examiner Not yet assigned	Bac H. Au				
Atty. Docket No. A35413-PCT-USA (070050.2717)		Serial No. 10/525,297															
Applicant James S. Im																	
Filing Date 02/15/2005	Group 28++ 2822																
Examiner Not yet assigned	Bac H. Au																

Exam Initial	No.	OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)
/BA/	154	Im <i>et al.</i> , "On the Super Lateral Growth Phenomenon Observed in Excimer Laser-Induced Crystallization of Thin Si Films," <i>Appl. Phys. Lett.</i> , Vol. 64 (17), p. 2303 (1994).
	155	Brochure from MicroLas Lasersystem, GmbH, "UV Optics Systems for Excimer Laser Based Micromaching and Marking", 1999.
	156	Ishida <i>et al.</i> , "Ultra-shallow boxlike profiles fabricated by pulsed ultraviolet-laser doping process", <i>J. Vac. Sci. Technol. B</i> 12(1), p. 399-403, 1994. (No month).
	157	Yoshimoto, <i>et al.</i> , "Excimer-Laser-Produced and Two-Dimensionally Position-Controlled Giant Si Grains on Organic SOG Underlayer", p. 285-286, <i>AM-LCD 2000</i> . No month.
	158	Ozawa <i>et al.</i> , "Two-Dimensionally Position-Controlled Excimer-Laser-Crystallization of Silicon Thin Films on Glassy Substrate", <i>Jpn. J. Appl. Phys.</i> vol. 38, Part 1, No. 10, p. 5700-5705, (1999). No month.
	159	I.W. Boyd, <i>Laser Processing of Thin Films and Microstructures, Oxidation, Deposition, and Etching of Insulators</i> (Springer--Verlag Berlin Heidelberg 1987).*
	160	N. Yamamuchi and R. Reif, <i>Journal of Applied Physics</i> , "Polycrystalline silicon thin films processed with silicon ion implantation and subsequent solid-phase crystallization: Theory, experiments, and thin-film transistor applications" -- April 1, 1994 -- Volume 75, Issue 7, pp. 3235-3257
	161	T. Noguchi, "Appearance of Single-Crystalline Properties in Fine-Patterned Si Thin Film Transistors (TFTs) by Solid Phase Crystallization (SPC)," <i>Jpn. J. Appl. Phys.</i> Vol. 32 (1993) L1584-L1587
	162	Ishihara <i>et al.</i> , "A Novel Double-Pulse Excimer-Laser Crystallization Method of Silicon Thin-Films," <i>Japanese Journal of Applied Physics</i> , Publication Office Japanese Journal of Applied Physics, Tokyo, Japan, vol. 34, no. 8A, August 1995, pp. 3976-3981
✓	163	Kim, H. J., "Excimer-Laser-Induced Crystallization of Amorphous Silicon Thin Films", Ph. D. Dissertation Abstract, Columbia University, 1996.*

NY02:531132.1

Examiner

/Bac Au/

Date Considered

07/31/2007

\* Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.